

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED TYPE

# 2SC5466

DYNAMIC FOCUS APPLICATIONS

HIGH VOLTAGE SWITCHING APPLICATIONS

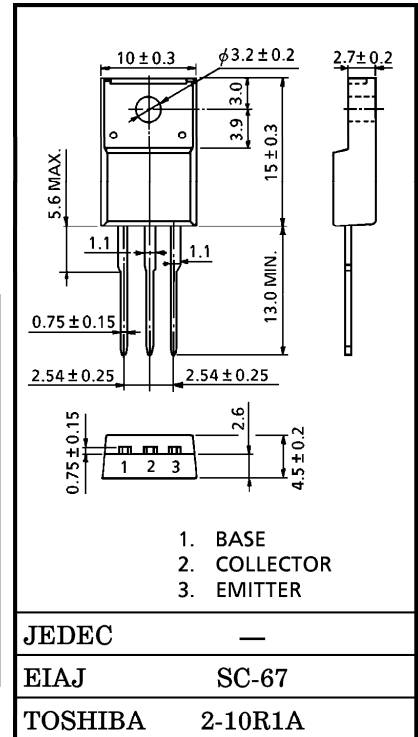
HIGH VOLTAGE AMPLIFIER APPLICATIONS

- High Voltage :  $V_{CEO} = 800\text{ V}$

MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{CBO}$	800	V
Collector-Emitter Voltage	$V_{CEO}$	800	V
Emitter-Base Voltage	$V_{EBO}$	5	V
Collector Current	$I_C$	50	mA
Base Current	$I_B$	25	mA
Collector Power Dissipation	$P_C$	$T_a = 25^\circ\text{C}$ 2.0	W
		$T_c = 25^\circ\text{C}$ 10	
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-55~150	$^\circ\text{C}$

Unit in mm



ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ\text{C}$ )

Weight : 1.7 g

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{CBO}$	$V_{CB} = 640\text{ V}, I_E = 0$	—	—	1.0	$\mu\text{A}$
Emitter Cut-off Current	$I_{EBO}$	$V_{EB} = 5\text{ V}, I_C = 0$	—	—	10	$\mu\text{A}$
DC Current Gain	$h_{FE}$	$V_{CE} = 5\text{ V}, I_C = 7\text{ mA}$	15	—	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 20\text{ mA}, I_B = 4\text{ mA}$	—	—	1.0	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 20\text{ mA}, I_B = 4\text{ mA}$	—	—	1.5	V
Transition Frequency	$f_T$	$V_{CE} = 10\text{ V}, I_C = 3\text{ mA}$	—	5.5	—	MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB} = 100\text{ V}, f = 1\text{ MHz}$	—	2.2	—	pF

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